

By: Nobuhiko HAYASHI et al.  
Serial No. 09/898,043

Group Art Unit: 2826  
Examiner: Johannes P. Mondt

*BI Pwnd*  
said cladding layer of a first conduction type has a ridge portion, and  
the thickness of said cladding layer of a first conduction type being less than 0.3  $\mu$ m.

*BD*  
29. (Amended) The nitride based semiconductor laser device according to claim 25, wherein  
the thickness of said ridged portion is less than 0.3  $\mu$ m.